

NPN BUY69A

MULTIEPITAXIAL MESA NPN

The BUY69A is silicon multiepitaxial mesa NPN transistor in Jedec TO-3. They are intended for horizontal deflection output stage of CTV receivers and high voltage, fast switching and industrial applications.

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V _{CEO}	Collector-Emitter Voltage	I _B = 0	400	V
V_{EBO}	Emitter-Base Voltage	$I_C = 0$	8	V
V _{CES}	Collector-Emitter Voltage	$I_C = 0$	1000	V
Ic	Collector Current		10	Α
I _{CM}	Collector Peak Current	$t_p = 10ms$	15	Α
I _B	Base Current		3	Α
Pt	Total Power Dissipation	$@ T_C = 25^{\circ}C$	100	W
TJ	Junction Temperature		200	°C
T _{Stg}	Storage Temperature		-65 to +200	°C

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJC}	Thermal Resistance, Junction to Case	1.75	°C/W



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage (*)	I _C =100 mA	400	-	-	V
V _{CBO}	Collector-Emitter	$I_C=1 \text{ mA}$ $I_E=0$	1000	-	-	V
I _{EBO}	Emitter Cutoff Current	V _{CE} =8 V I _C =0	-	-	1	mA
I _{CES}	Collector Cutoff Current	$V_{CE} = V_{CES}$ $V_{BE} = 0$	-	-	1	mA
h _{FE}	DC Current Gain (*)	I _C =2.5 A V _{CE} =10 V	15	-	-	-
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C =8 A I _B =2.5 A	-	-	3.3	V
V _{BE(SAT)}	Base-Emitter saturation Voltage (*)	I _C =8 A I _B =2.5 A	-	-	2.2	V
f _T	Transition Frequency	I _C =0.5 A V _{CE} =10 V	-	10	-	MHz
I _{s/b}	Second Breakdown Collector Current (**)	V _{CE} =25 V	4	-	-	Α
t _{on}	Turn-on time	I _C =5 A , I _B =1 A V _{CC} =250 V	-	0.2	-	
ts	Storage time	I _C =5 A , V _{CC} =250 V I _{B1} =1A , -I _{B2} =1 A	-	1.7	-	
t _f	File time	I _C =5 A , V _{CC} =-250 V I _{B1} =1A , -I _{B2} =1 A	-	0.3	-	μs
t _f	File time	I _C =8 A , V _{CC} =-40 V I _{B1} =2.5A , -I _{B2} =2.5 A			1	

^(*) Pulse Duration = 300 μs, Duty Cycle <= 1.5%

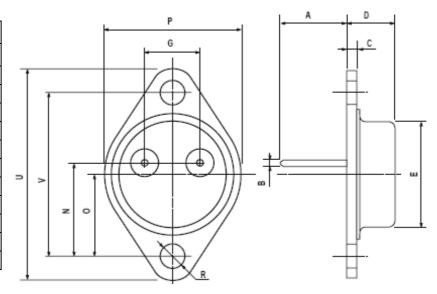
^(**) Pulsed :1s, non repetitive pulse



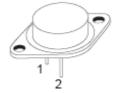
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)			
	min	max	
A	11	13.10	
В	0.97	1.15	
С	1.5	1.65	
D	8.32	8.92	
F	19	20	
G	10.70	11.1	
N	16.50	17.20	
Р	25	26	
R	4	4.09	
U	38.50	39.30	
V	30	30.30	



Pin 1:	Base
Pin 2 :	Emitter
Case:	Collector



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